

Figure 1

Figure 2

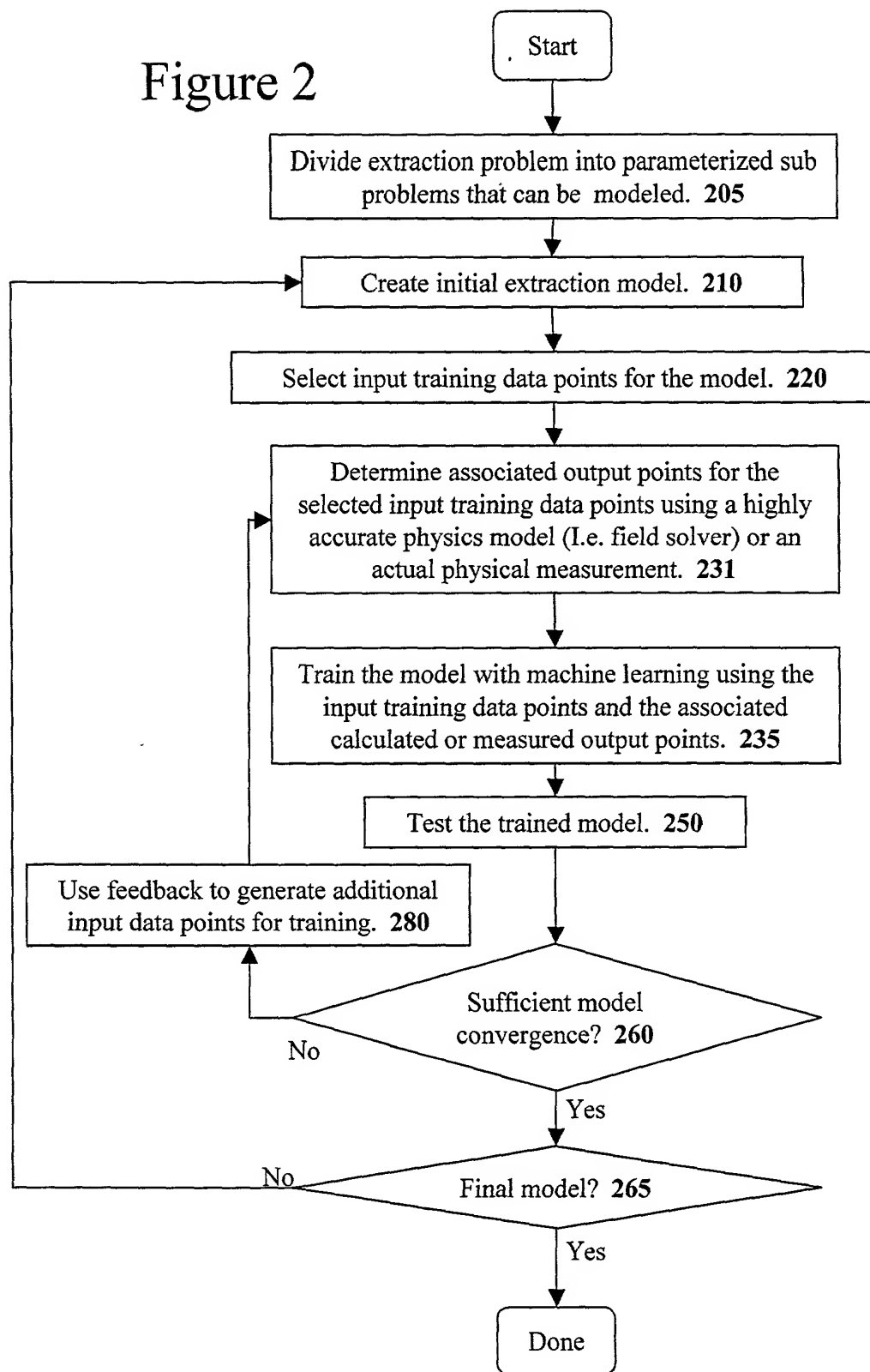


Figure 3

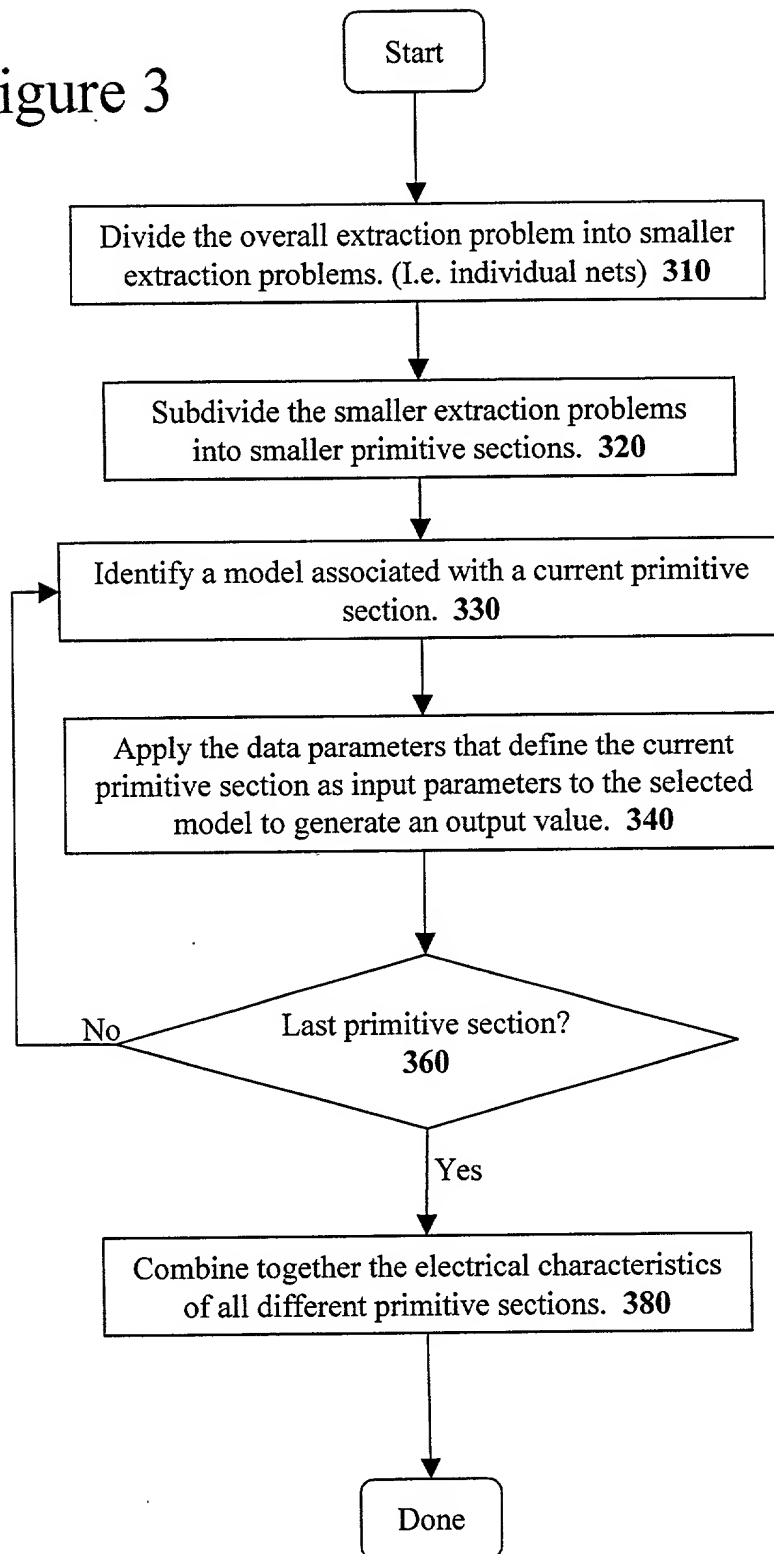


Figure 4

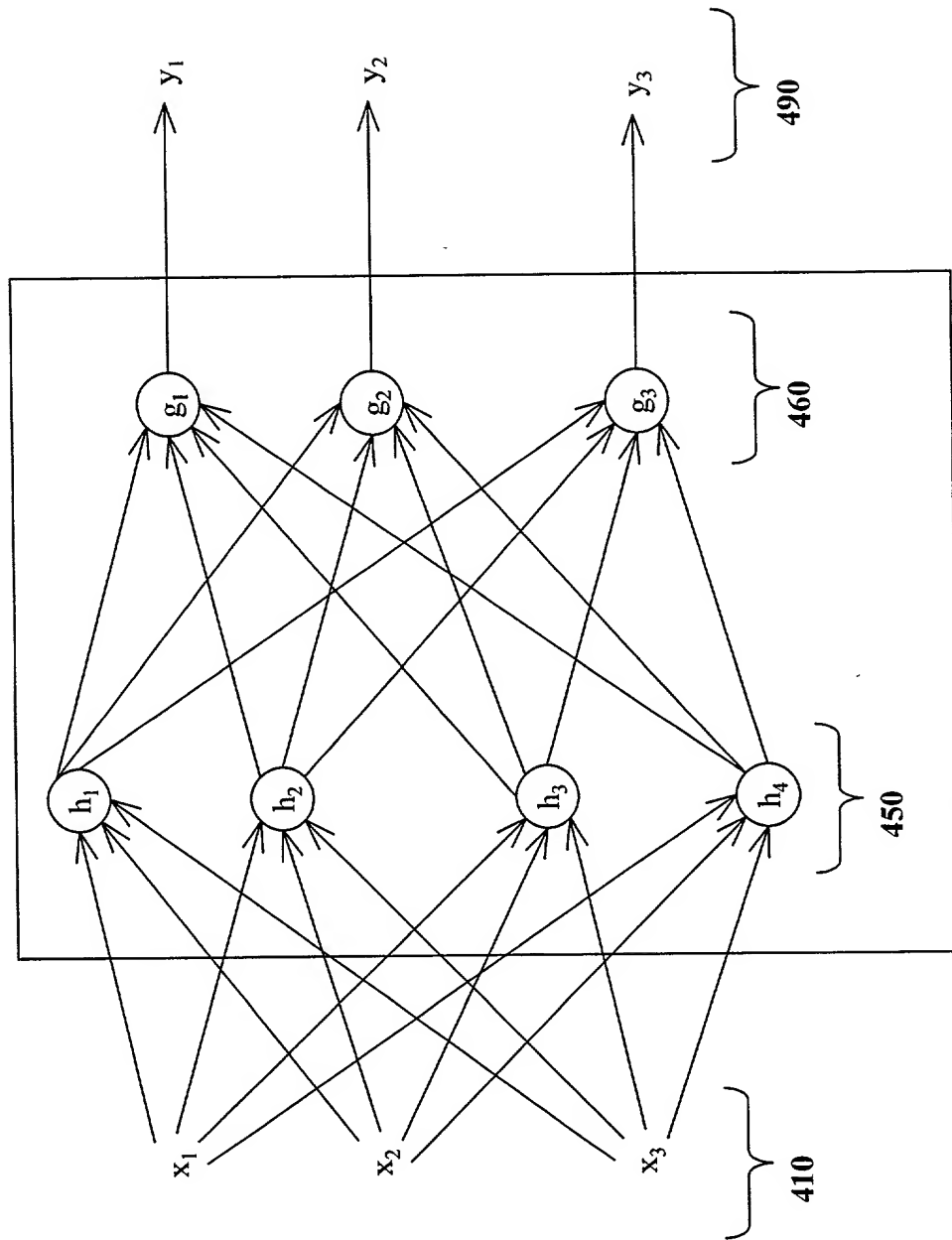
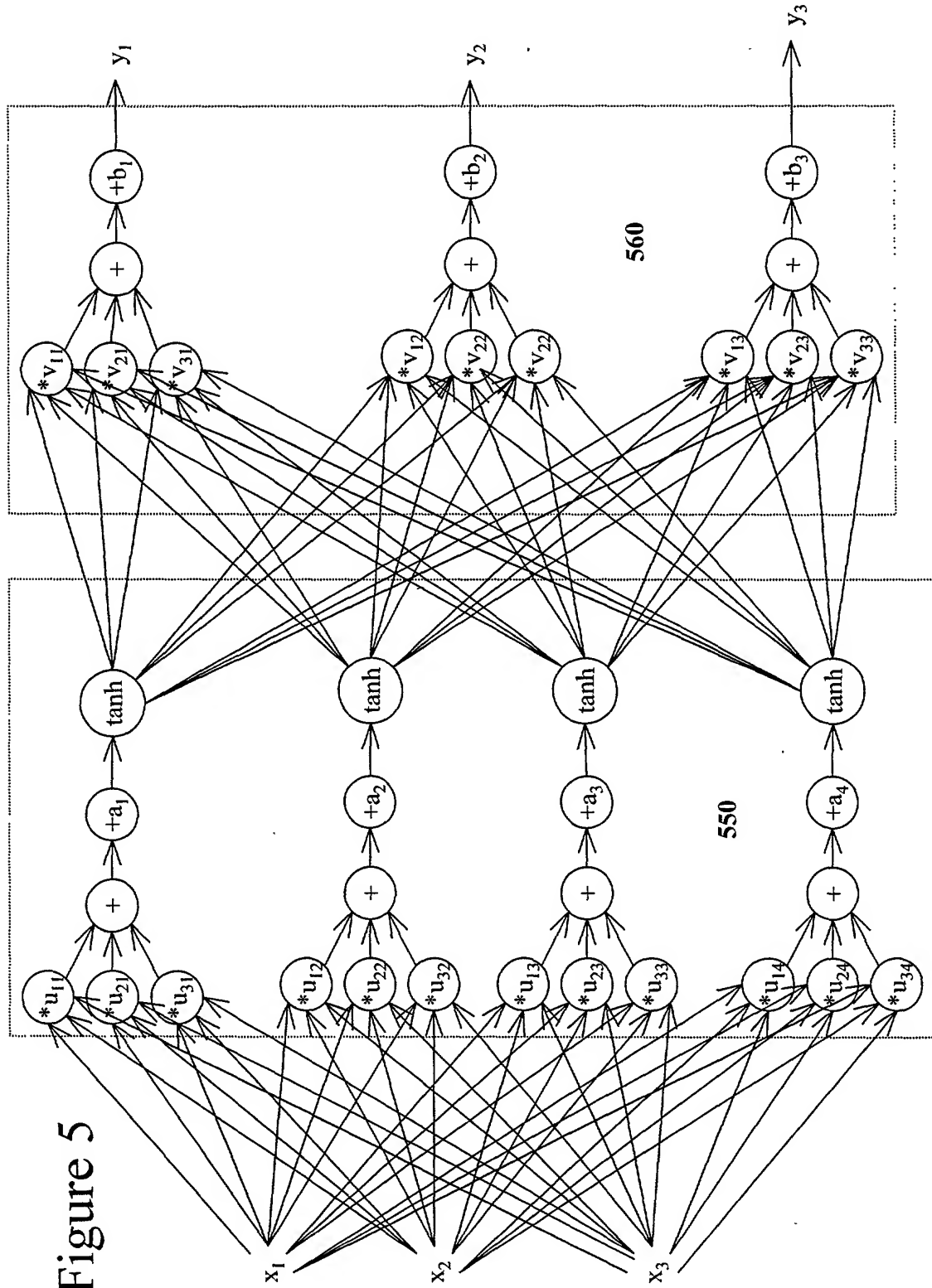


Figure 5



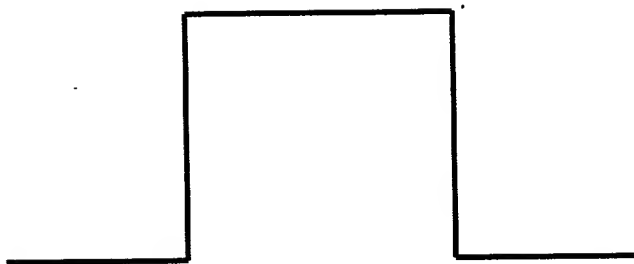


Figure 6a

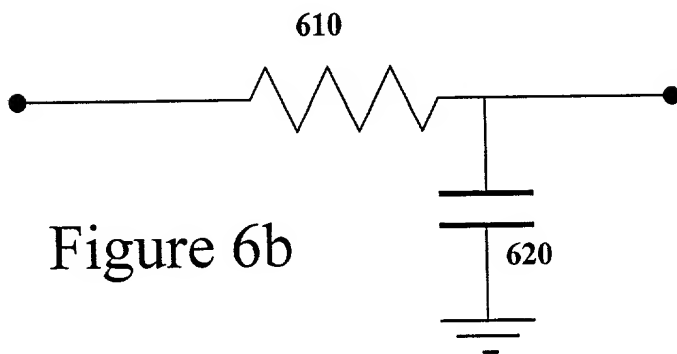


Figure 6b

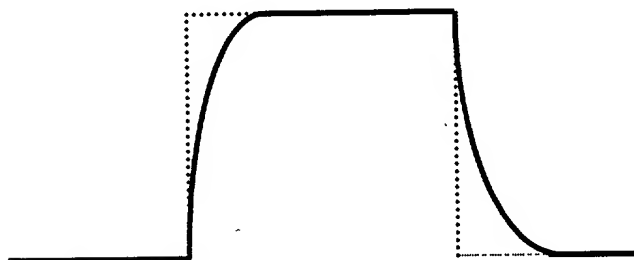


Figure 6c

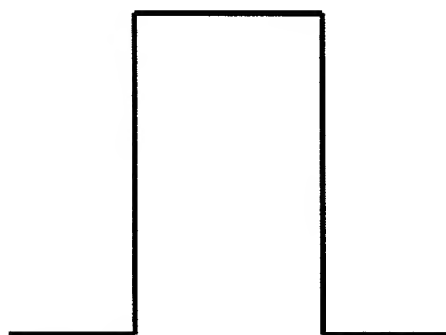


Figure 7a

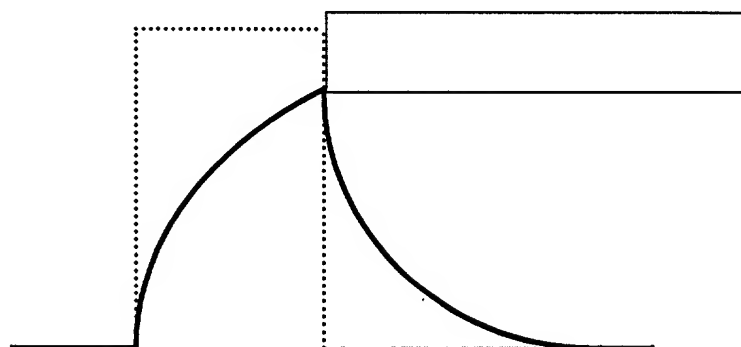


Figure 7b

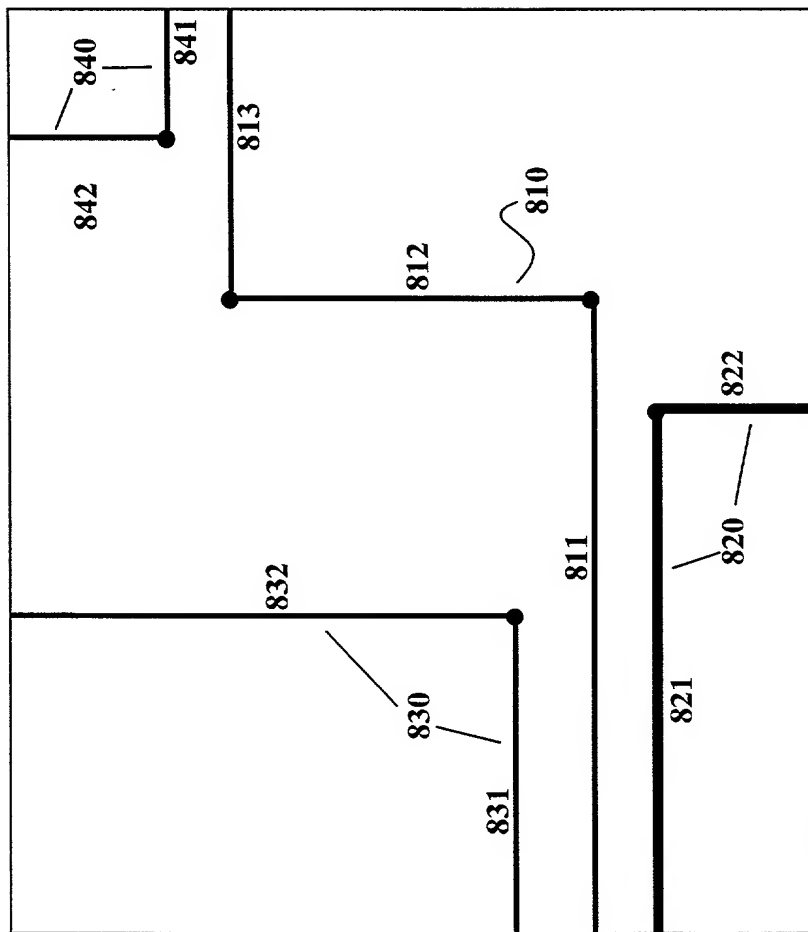


Figure 8A



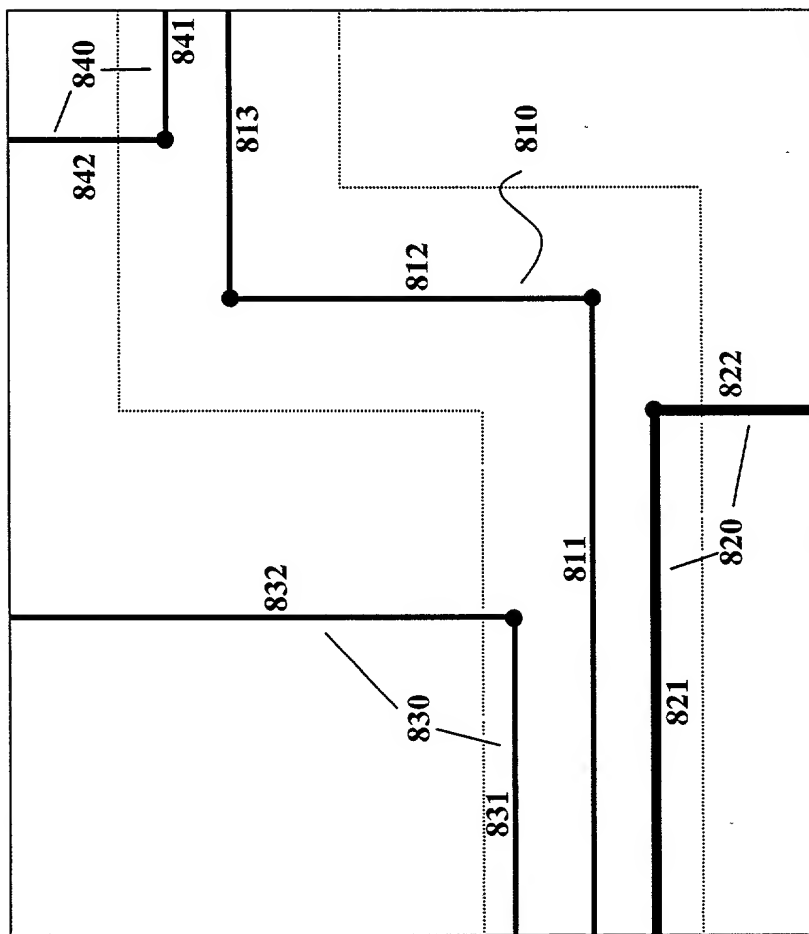


Figure 8B

Figure 8C

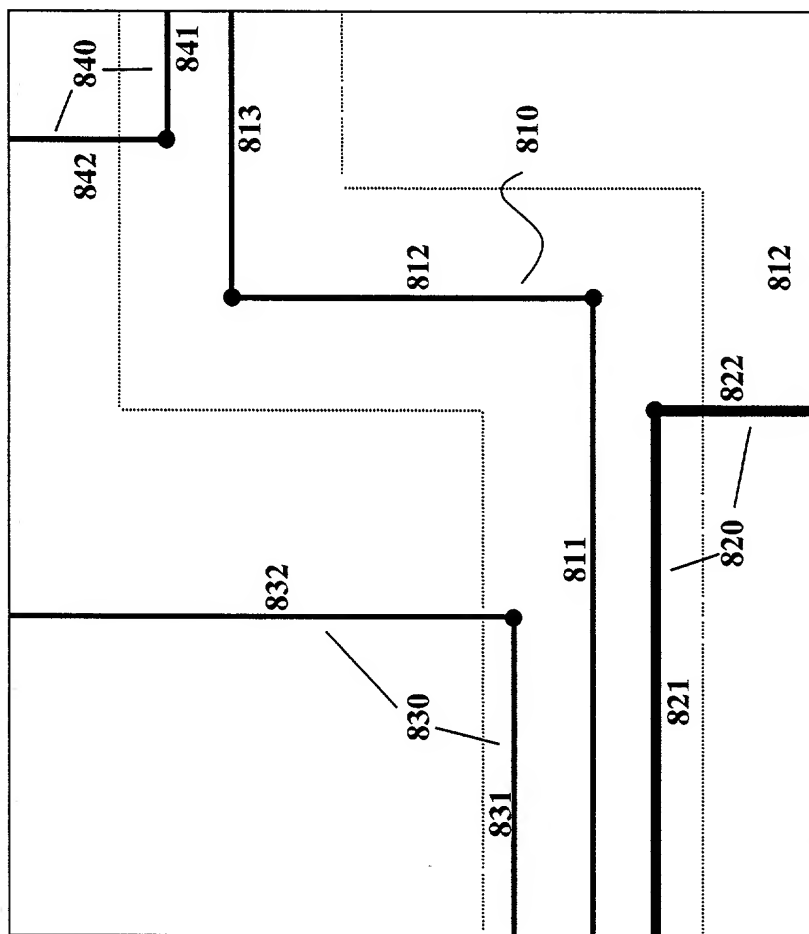


Figure 8D

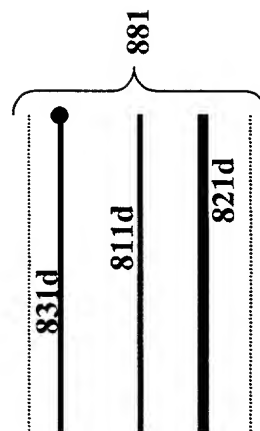
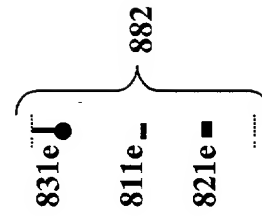
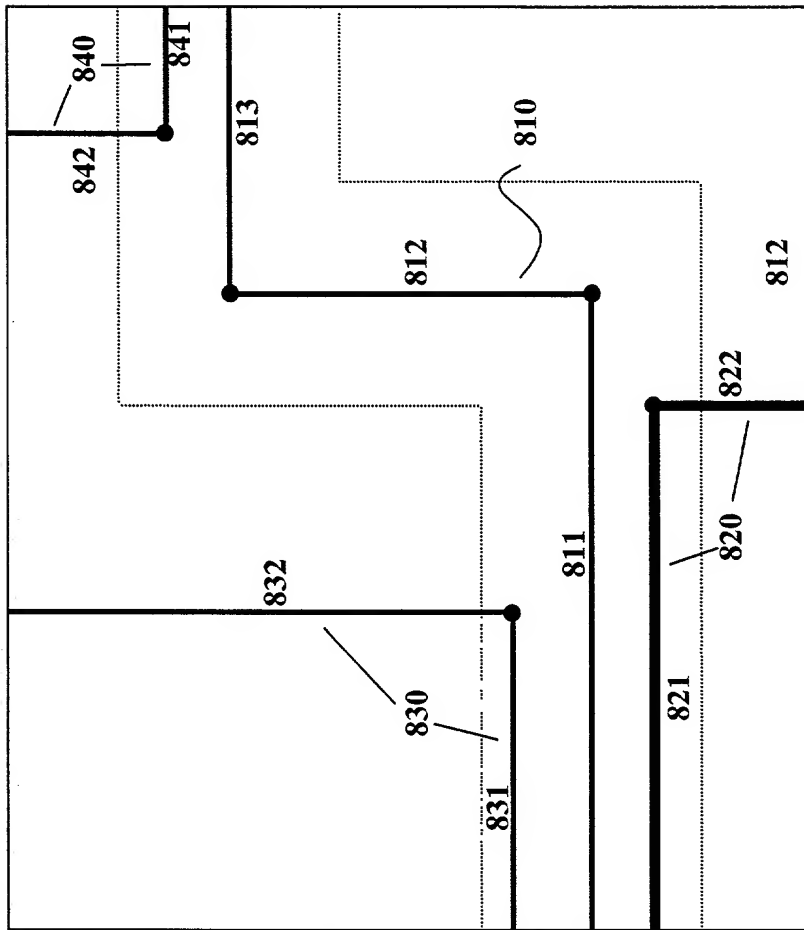


Figure 8E



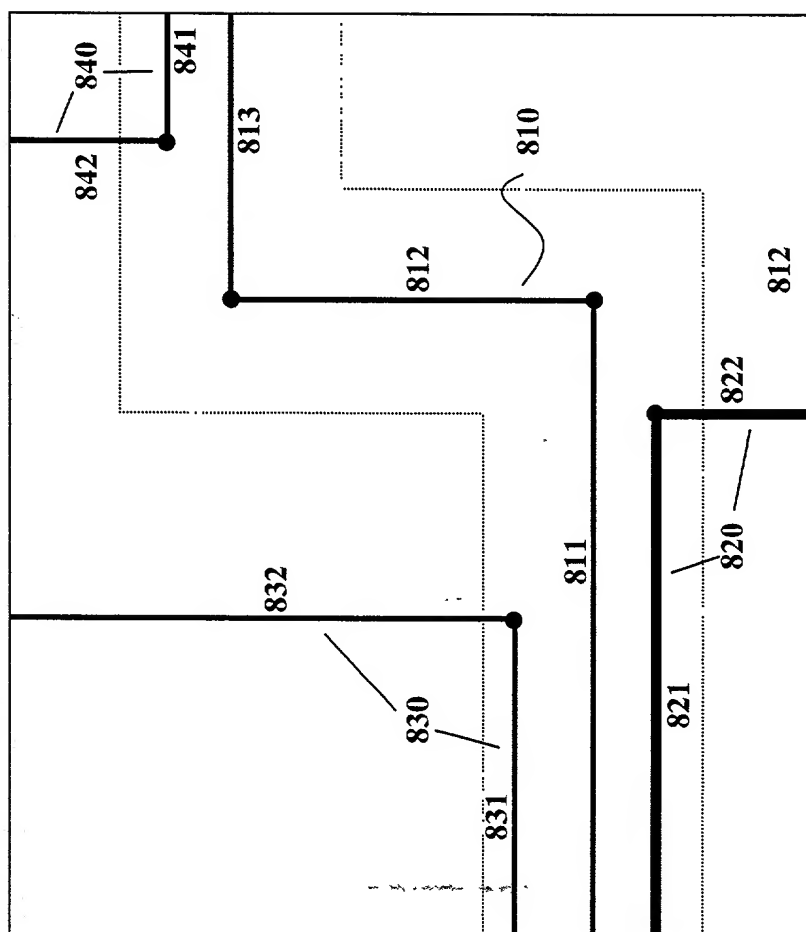
[illegible]

Figure 8F

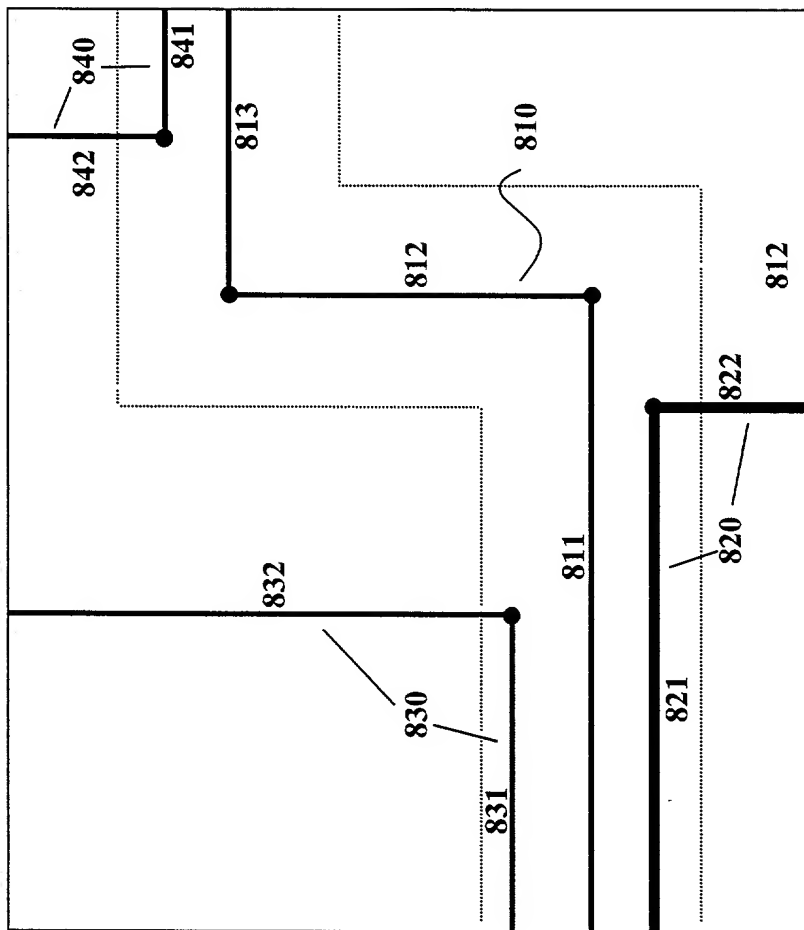
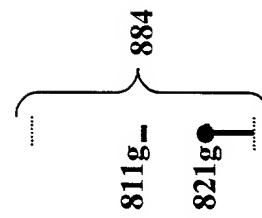


Figure 8G



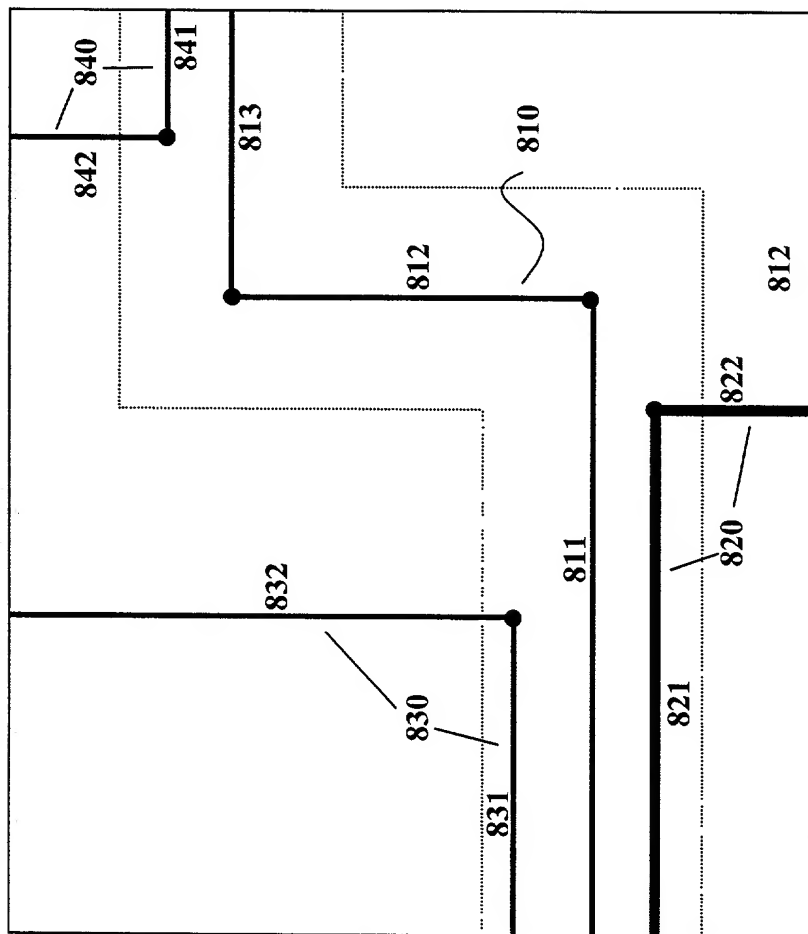


Figure 8H

FIG. 9A is a perspective view of a device 900 in accordance with the present invention. The device 900 includes a substrate 910, a first layer 920, a second layer 930, and a third layer 940. The first layer 920 is disposed on the substrate 910, the second layer 930 is disposed on the first layer 920, and the third layer 940 is disposed on the second layer 930. The device 900 is configured to perform a function.

Figure 9A

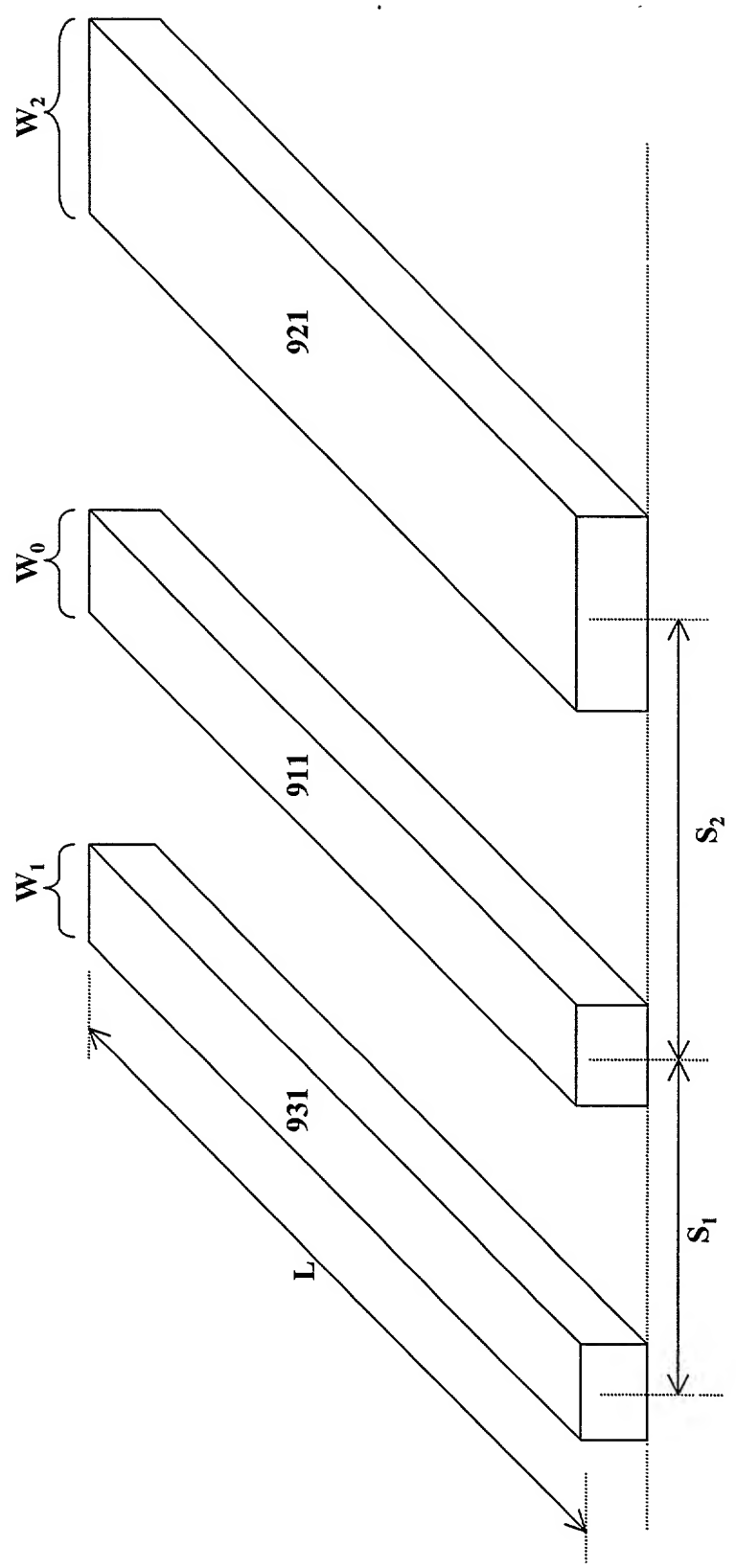




Figure 9B

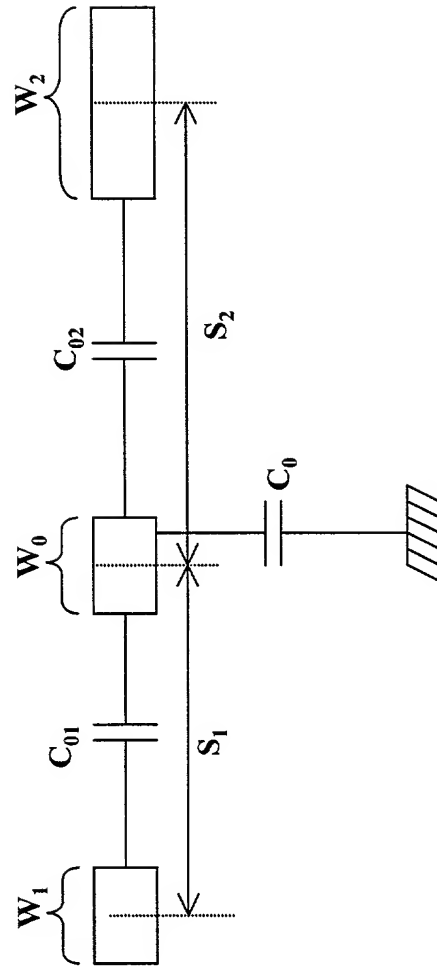
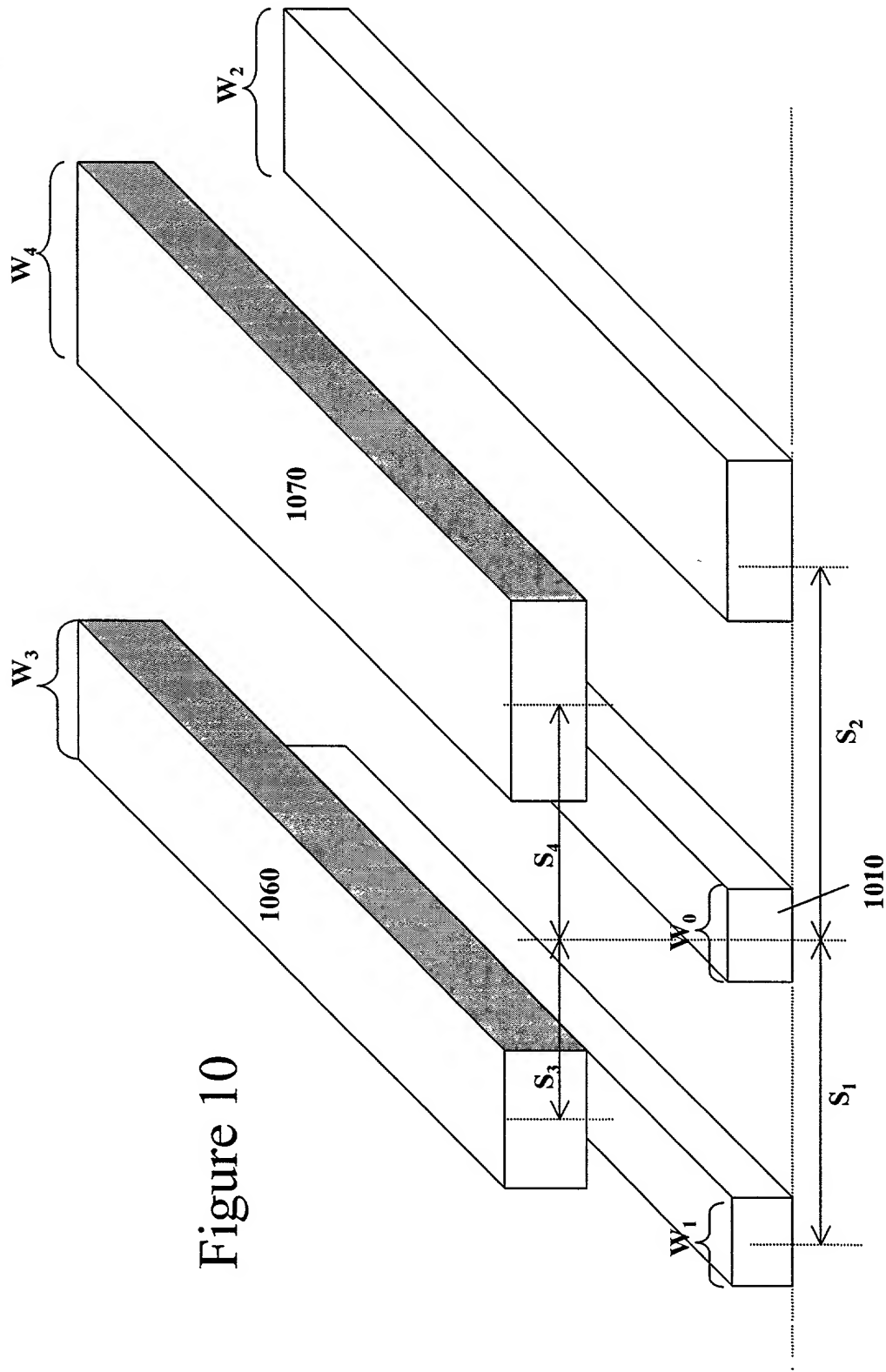


FIG. 10 is a perspective view of a device 1000 in accordance with the present invention. The device 1000 includes a base 1010, a first layer 1060, and a second layer 1070. The first layer 1060 is disposed on the base 1010, and the second layer 1070 is disposed on the first layer 1060. The first layer 1060 and the second layer 1070 are both made of a material having a high thermal conductivity. The first layer 1060 and the second layer 1070 are both made of a material having a high thermal conductivity. The first layer 1060 and the second layer 1070 are both made of a material having a high thermal conductivity.

Figure 10



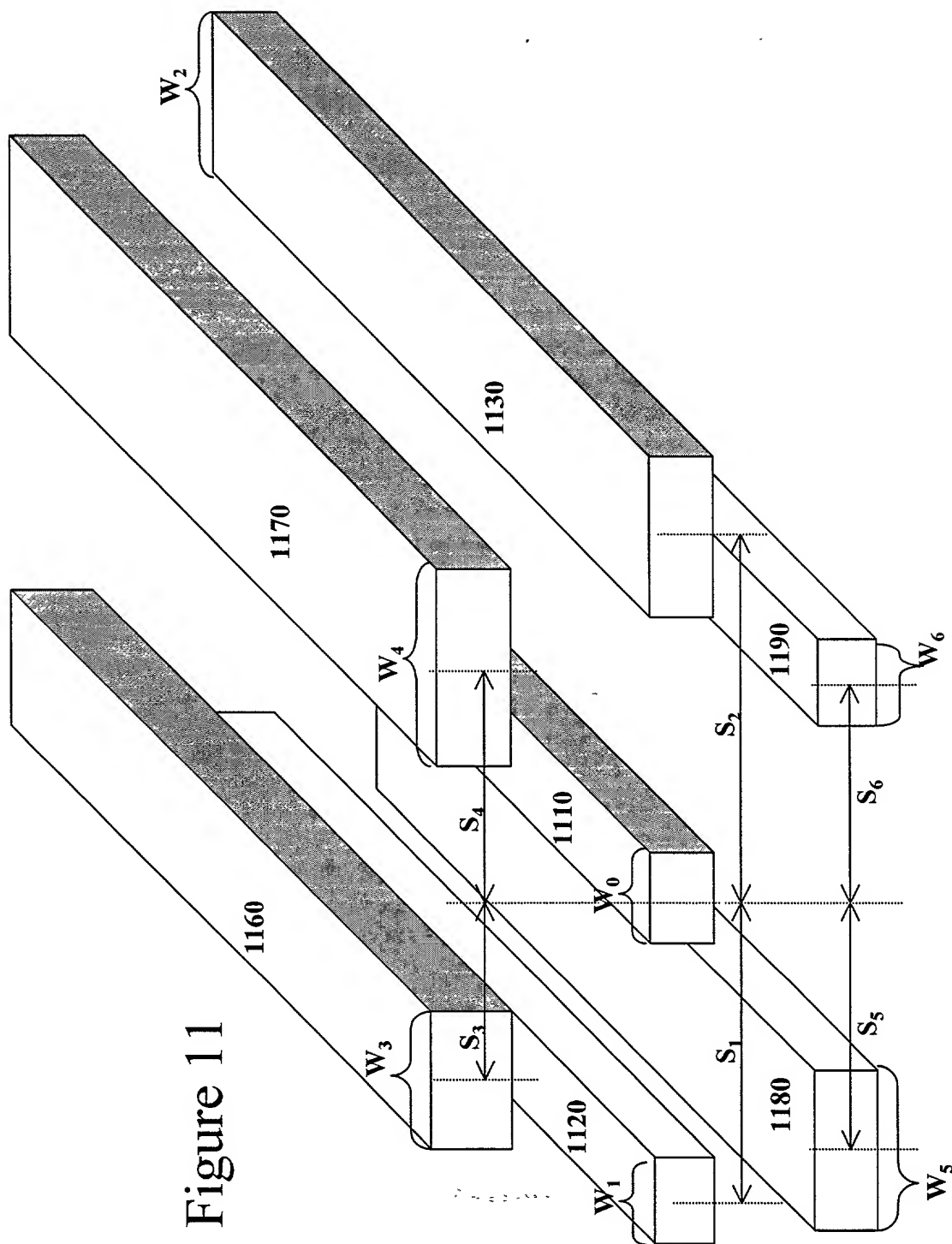
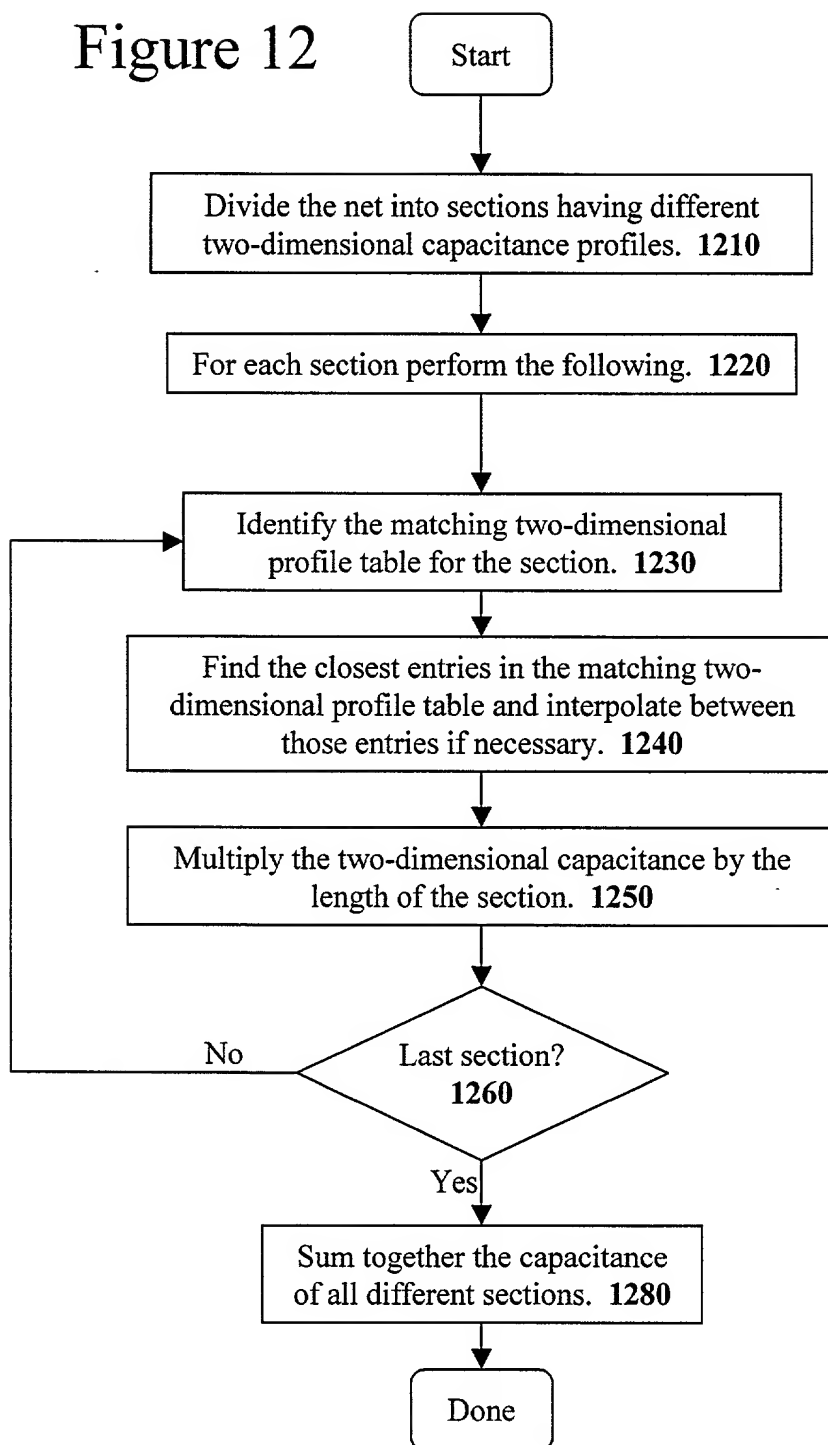


Figure 11

Figure 12



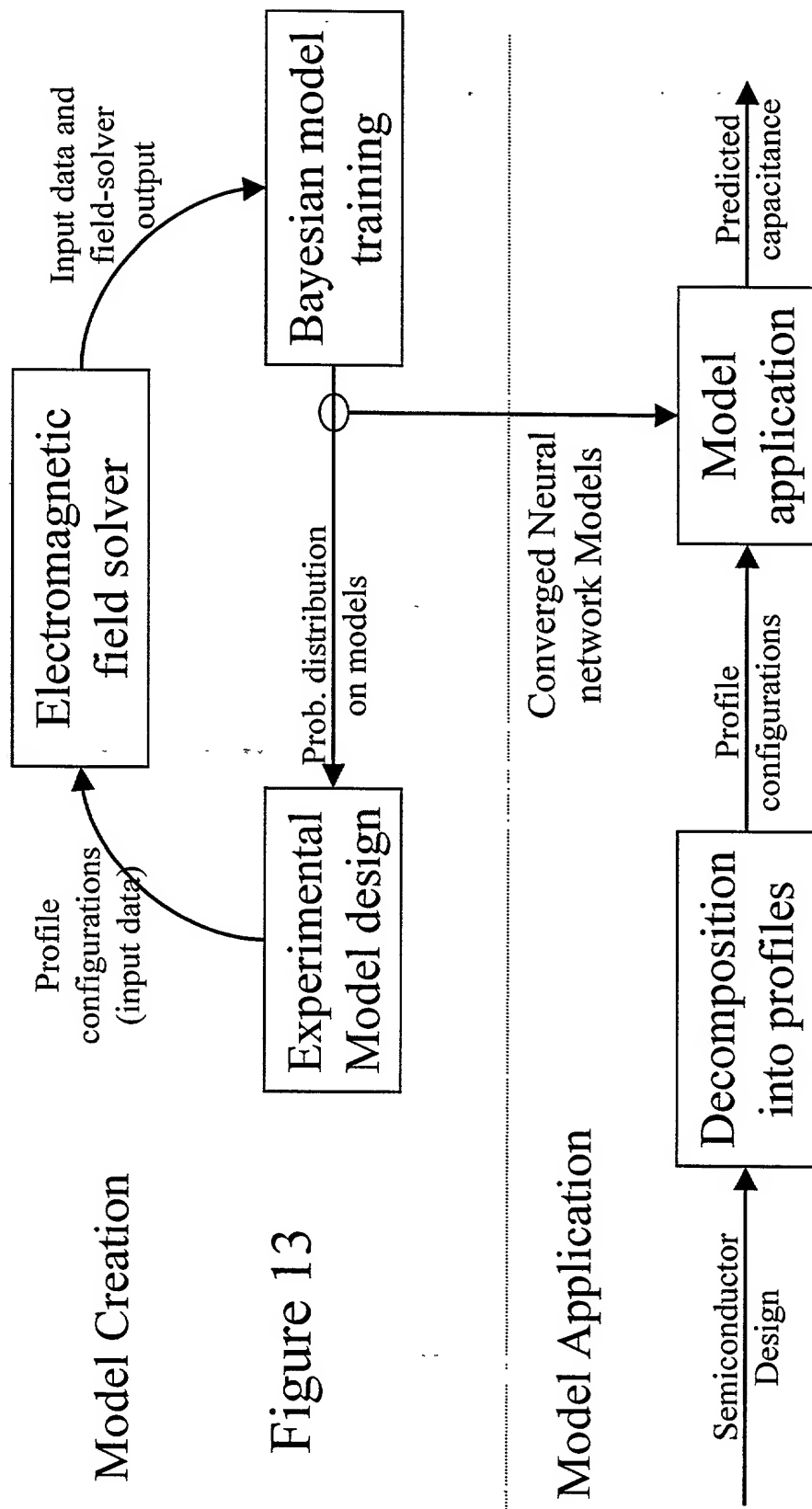


Figure 13

Figure 14

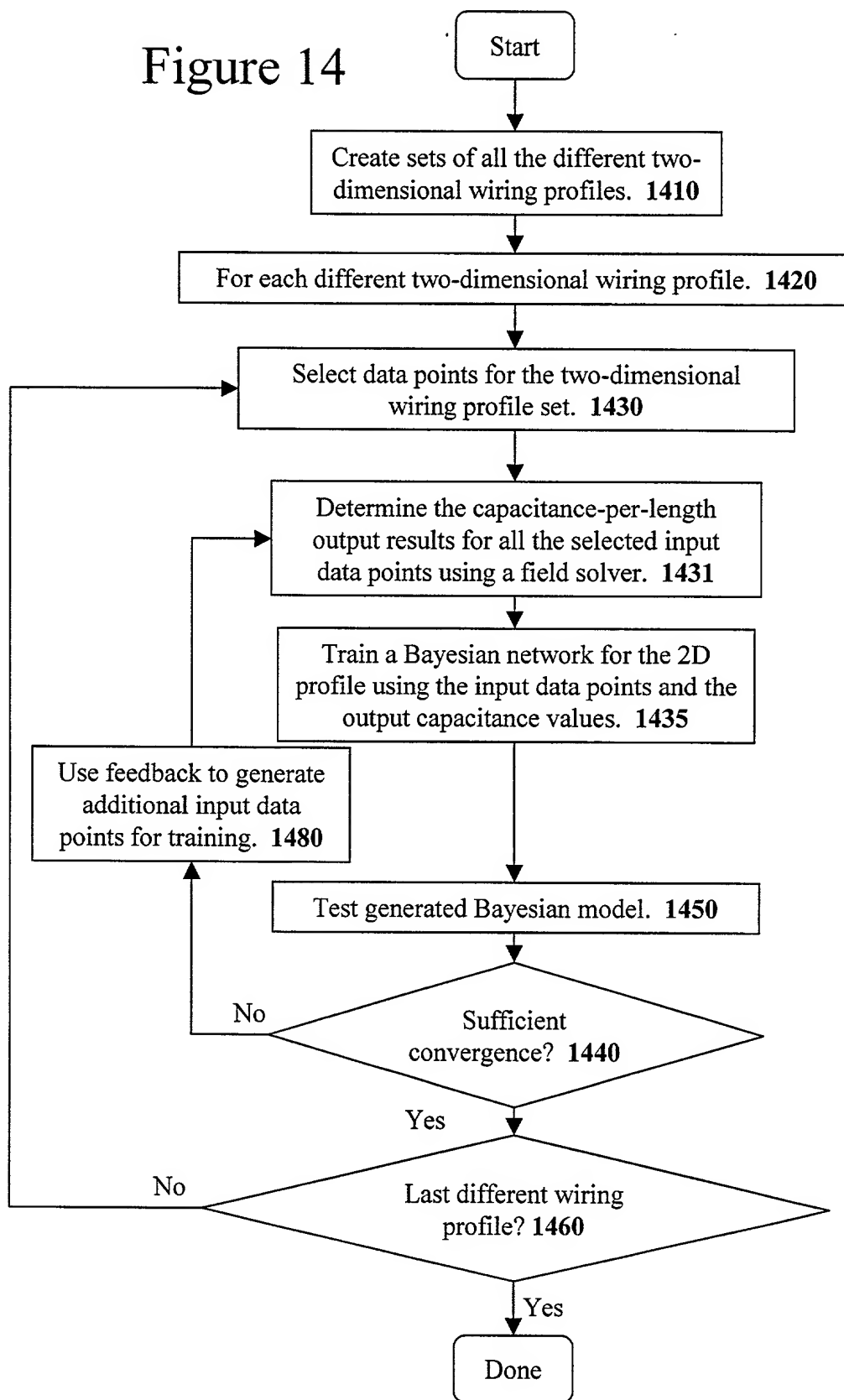
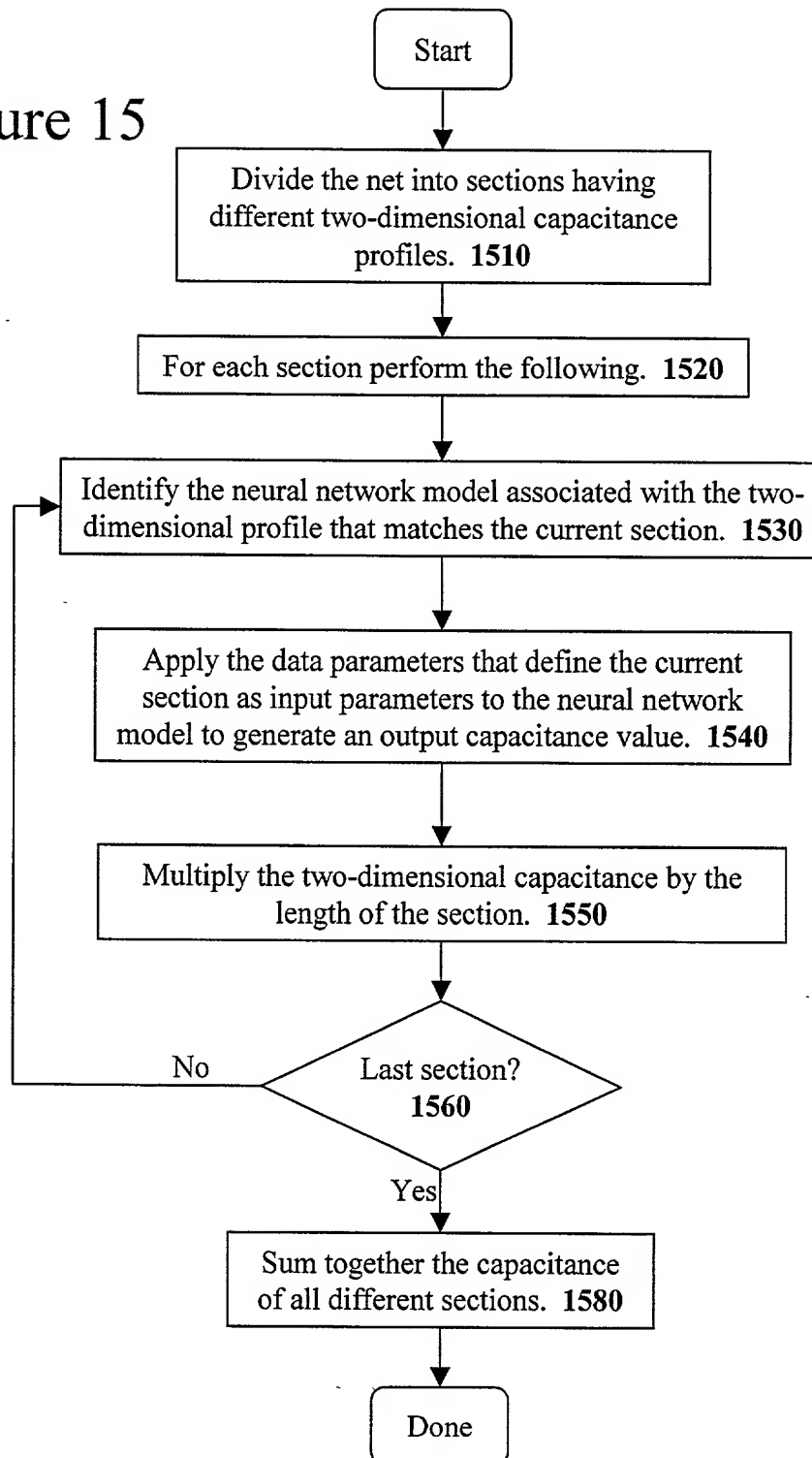


Figure 15



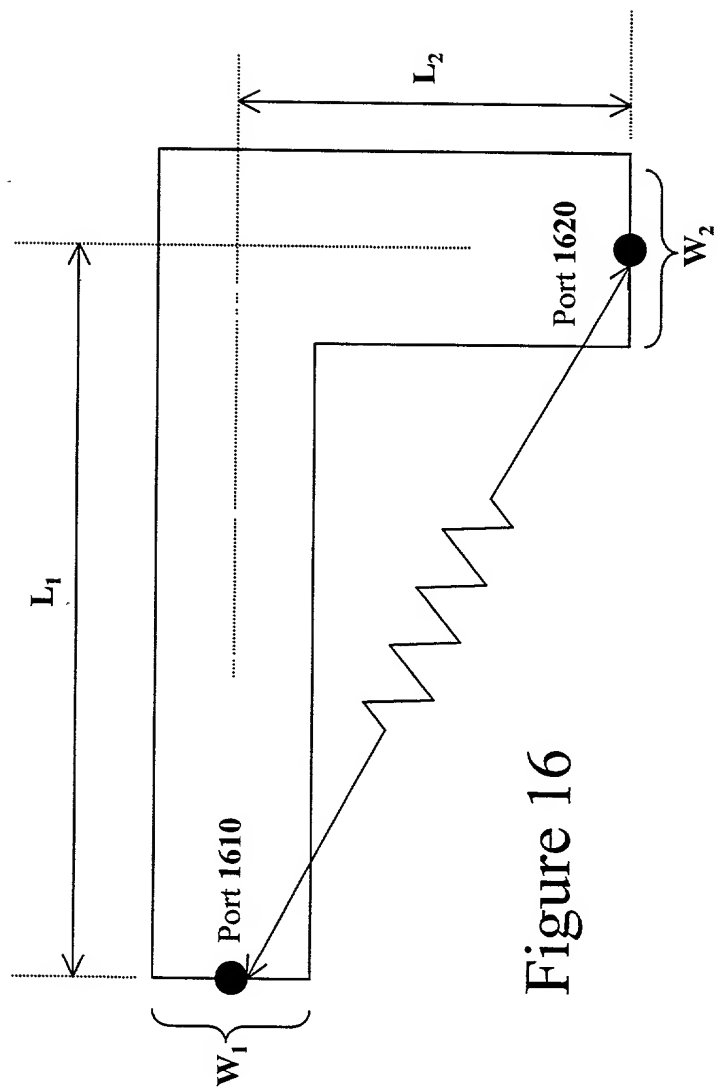


Figure 16



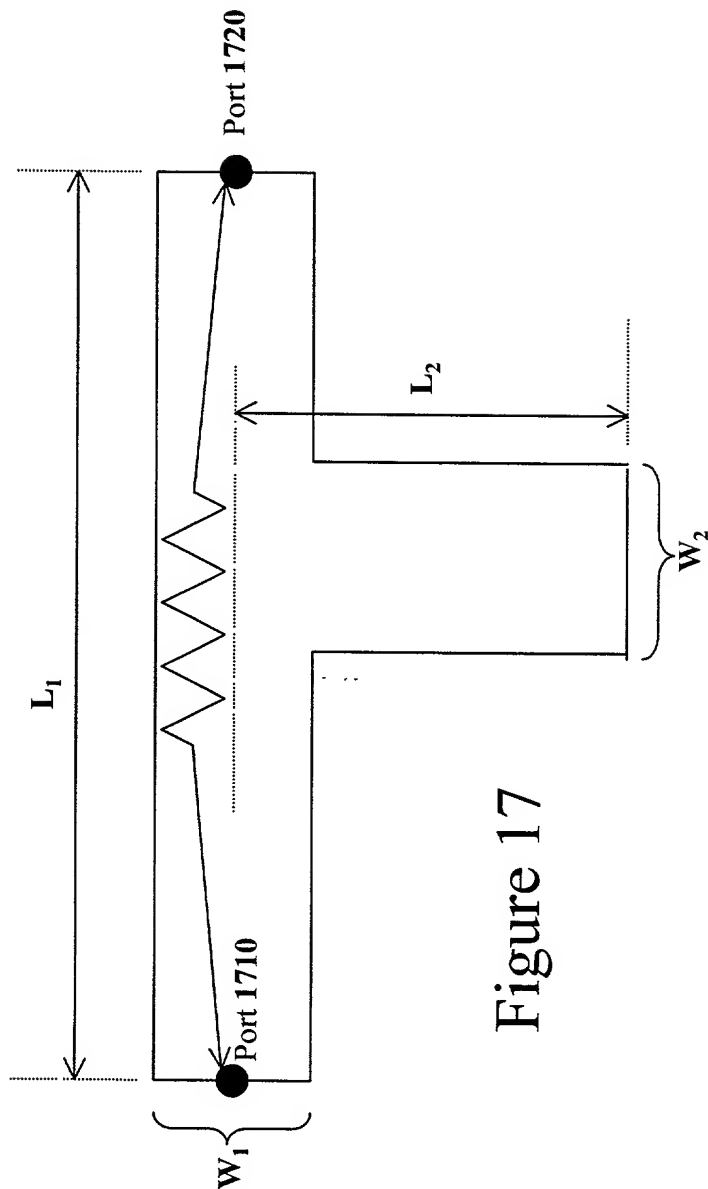


Figure 17

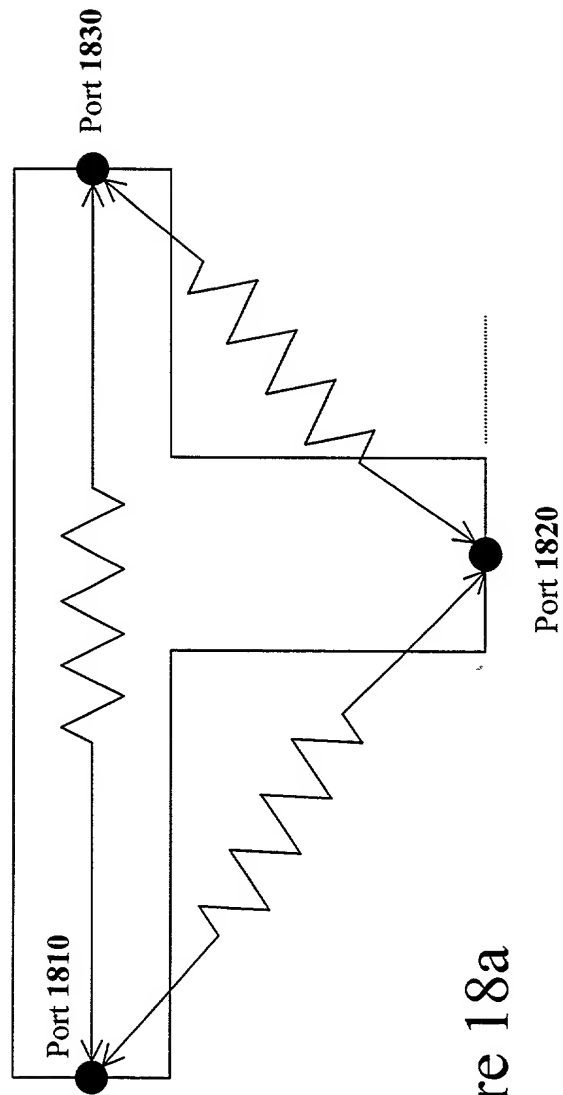


Figure 18a

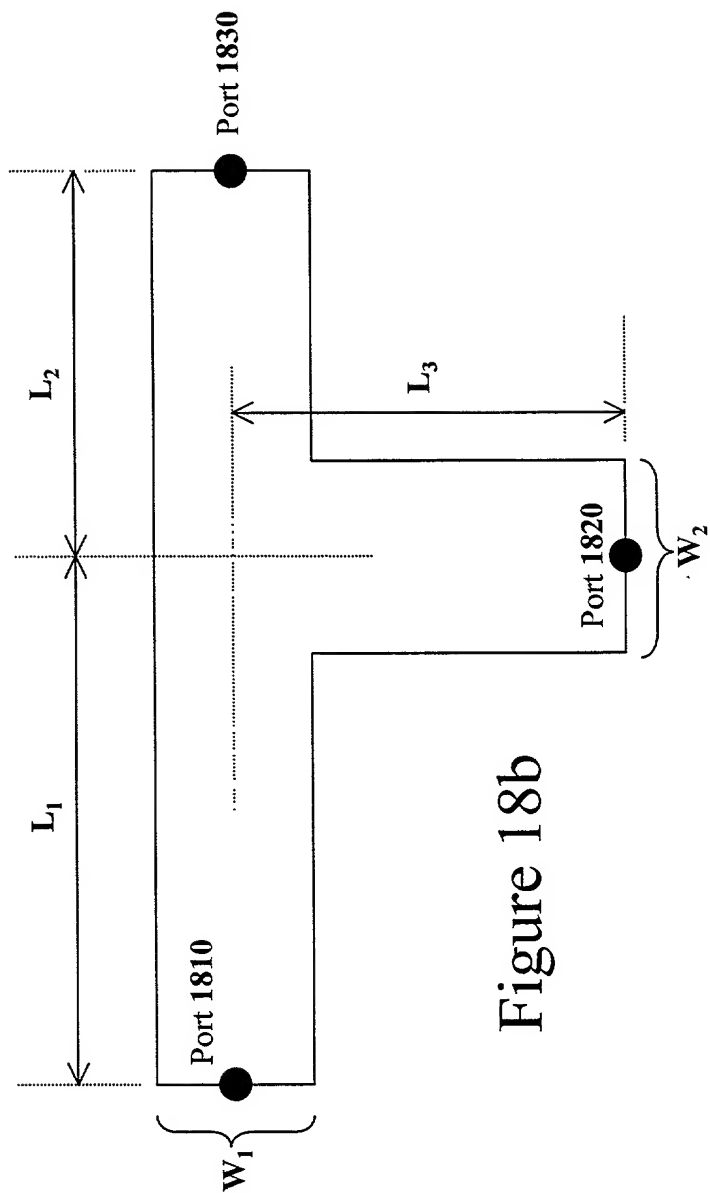


Figure 18b

Figure 19a

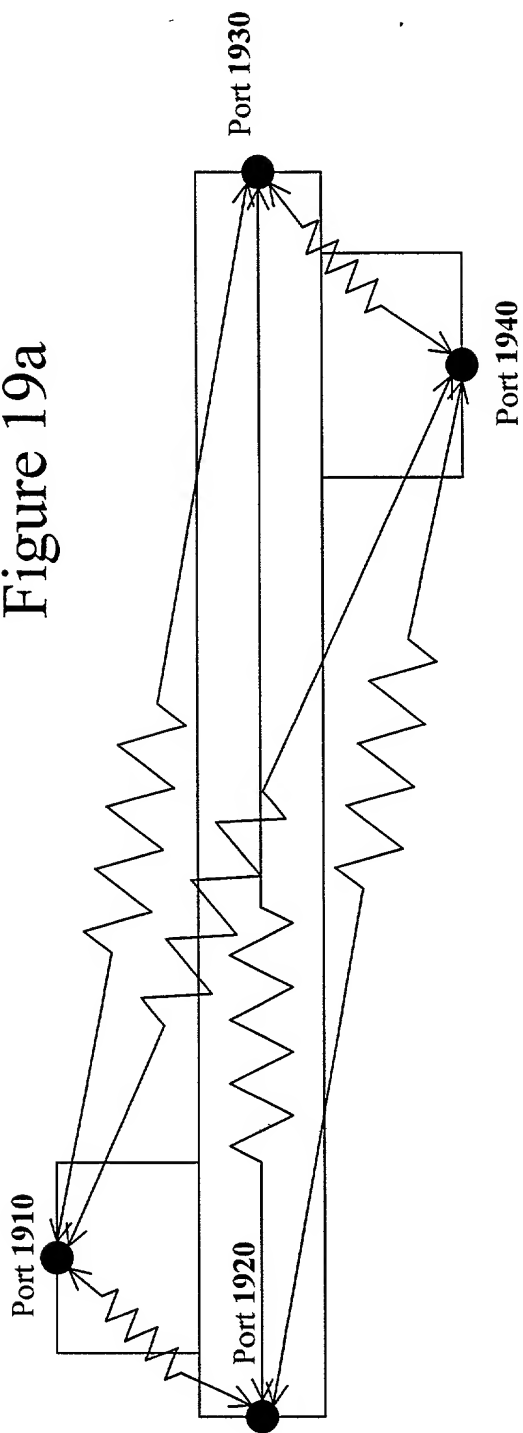


Figure 19b

